

## 双通道，高压 - 多级输出完全集成超声波发射机

 查询样品: **TX517**

### 特性

- 输出电压:
  - 差分模式下, 高达 **200Vpp**
- 峰值输出电流: **±2.5A**
- 多级输出
  - 差分: **17级**
  - 单端: **5级**
- 集成:
  - 电平转换器
  - 驱动器
  - 高压输出级
  - **CW** 输出
- **TX** 输出更新率
  - 最高 **100MSPS**
- 最小外部组件
- 小型封装: **13 x 13mm**球状引脚栅格阵列(**BGA**)封装

### 应用范围

- 医疗超声波
- 高压信号生成器

### 说明

TX517 是一款完全集成, 双通道, 高压发射器。它特别设计用于高要求的医疗超声波应用, 此应用要求一个多级高压脉冲波形。此输出级设计传送典型值为 $\pm 2.5A$ 的峰值输出电流, 摆幅 $200Vpp$ 。

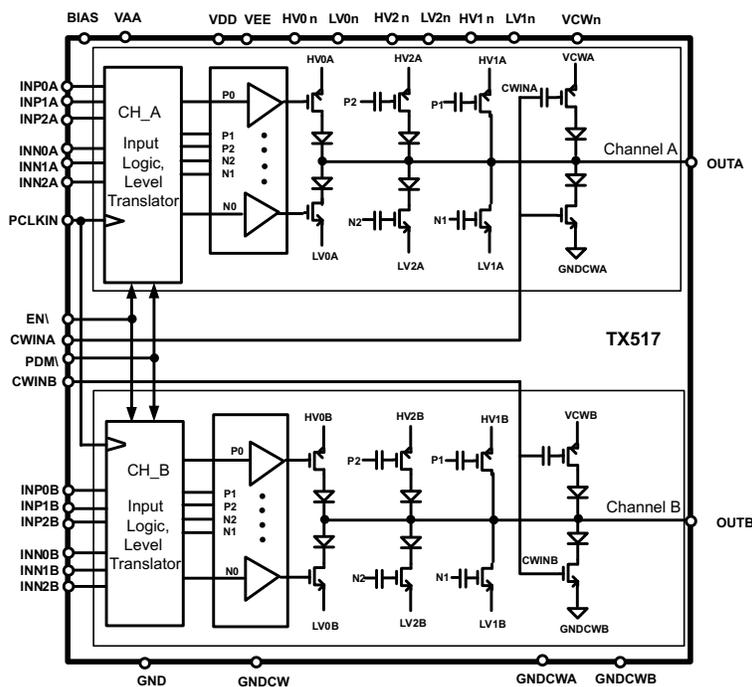
TX517 是一个完整发射器解决方案, 此方案每通道含低压输入逻辑, 电平转换器, 栅极驱动器和P通道, N通道金属氧化物半导体场效应晶体管 (MOSFET)。

TX517 还包含一个 CW 输出级。

TX517 采用球状引脚栅格阵列 (BGA) 封装, 此封装是无铅 (RoHS兼容) 并且绿色环保。它的额定运行温度为 $0^{\circ}C$  至  $85^{\circ}C$ 。

#### 17个电平脉冲发生器芯片:

当与变压器一同使用时, 此芯片包含 2 个 5 级通道来形成一个单一17级发射器单元。此器件设计用于驱动处于不同输出电平上的变送器, 而且能调制输出脉冲宽度以获得脉宽调制频谱定型的额外的灵活性。



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

**PACKAGING/ORDERING INFORMATION<sup>(1)</sup>**

PACKAGED DEVICES	PACKAGE TYPE	PACKAGE MARKING	TRANSPORT MEDIA, QUANTITY	ECO STATUS <sup>(2)</sup>
TX517ZCQ	BGA-144	TX517	Tray	Pb-Free, Green

(1) NOTE: These Packages conform to Lead-Free and Green Manufacturing Specifications

(2) Eco-Status information: Additional details including specific material content can be accessed at [www.ti.com/leadfree](http://www.ti.com/leadfree)

**GREEN:** Ti defines Green to mean Lead (Pb)-Free and in addition, uses less package materials that do not contain halogens, including bromine (Br), or antimony (Sb) above 0.1% of total product weight.

**N/A:** Not yet available Lead (Pb)-Free; for estimated conversion dates, go to [www.ti.com/leadfree](http://www.ti.com/leadfree).

**Pb-FREE:** Ti defines Lead (Pb)-Free to mean RoHS compatible, including a lead concentration that does not exceed 0.1% of total product weight, and, if designed to be soldered, suitable for use in specified lead-free soldering processes.

**DEVICE INFORMATION**

**BGA-144 PINS  
TOP VIEW**

	1	2	3	4	5	6	7	8	9	10	11	12	
A	HV2B	GND	HV1B	HV0B	VCWB	ENI	VAAB	NC	NC	INP1B	INN1B	INP2B	A
B	NC	LV1B	LV1B	LV1B	LV1B	LV1B	GND	NC	NC	GND	VAAC	INN2B	B
C	OUTB	LV1B	LV1B	LV1B	LV1B	LV1B	CWINB	VEE	VEE	VEE	VEE	INN0B	C
D	NC	LV1B	LV1B	LV1B	LV1B	LV1B	GND	VEE	VEE	VEE	VEE	INP0B	D
E	LV2B	LV1B	LV1B	LV1B	LV1B	LV1B	VDD	VEE	VEE	VEE	VEE	PCLKIN	E
F	LV1B	LV1B	LV1B	LV1B	LV1B	LV1B	LV0B	VEE	VEE	VEE	VEE	GND	F
G	LV1A	LV1A	LV1A	LV1A	LV1A	LV1A	LV0A	VEE	VEE	VEE	VEE	VDD	G
H	LV2A	LV1A	LV1A	LV1A	LV1A	LV1A	VDD	VEE	VEE	VEE	VEE	CWINA	H
J	NC	LV1A	LV1A	LV1A	LV1A	LV1A	GND	VEE	VEE	VEE	VEE	INP0A	J
K	OUTA	LV1A	LV1A	LV1A	LV1A	LV1A	GND	VEE	VEE	VEE	VEE	INN0A	K
L	NC	LV1A	LV1A	LV1A	LV1A	LV1A	GND	NC	NC	GND	VAAD	INN2A	L
M	HV2A	GND	HV1A	HV0A	VCWA	PDM	VAAA	BIAS	NC	INP1A	INN1A	INP2A	M
	1	2	3	4	5	6	7	8	9	10	11	12	

**PIN FUNCTIONS**

PIN NAME	DESCRIPTION
<b>SUPPLIES</b>	
VAAx	Input Logic Supply (+2.5V)
VDD	+5V Driver Supply
VEE	–5V Driver Supply
HV0A, HV0B	Positive Supply of Low-voltage FET Output stage; Channel A and B
LV0A, LV0B	Negative Supply of Low-voltage FET Output stage; Channel A and B
HV2A, HV2B	Positive Supply of Intermediate voltage FET Output stage; this stage includes an internal de-glitcher circuit. Channel A and B
LV2A, LV2B	Negative Supply of Intermediate voltage FET Output stage; this stage includes an internal de-glitcher circuit. Channel A and B
HV1A, HV1B	Positive Supply of High-voltage FET Output stage; Channel A and B
LV1A, LV1B	Negative Supply of High-voltage FET Output stage; Channel A and B
VCWA, VCWB	Supply connections for CW FET output stage; Channel A and B
GND	Ground connection; Driver
GND <sub>CWA</sub> , GND <sub>CWB</sub>	Ground connection for CW FET output stage of Channel A and B
BIAS	Connect to VAA (+2.5V); used for internal biasing; high-impedance input
<b>INPUTS</b>	
INP0A, INP0B	Logic input signal for the Low-voltage P-FET stage of channel A and B; <b>Low = ON, High = OFF</b> . Controls HV0A, HV0B. High impedance input.
INN0A, INN0B	Logic input signal for the Low-voltage N-FET stage of channel A and B; <b>Low = OFF, High = ON</b> . Controls LV0A, LV0B. High impedance input.
INP2A, INP2B	Logic input signal for the Intermediate voltage P-FET stage of channel A and B; <b>Low = ON, High = OFF</b> . Controls HV2A, HV2B. High impedance input.
INN2A, INN2B	Logic input signal for the Intermediate Voltage N-FET stage of channel A and B; <b>Low = OFF, High = ON</b> . Controls LV2A, LV2B. High impedance input.
INP1A, INP1B	Logic input signal for the High-voltage P-FET stage of channel A and B; <b>Low = ON, High = OFF</b> . Controls HV1A, HV1B. High impedance input.
INN1A, INN1B	Logic input signal for the High-voltage N-FET stage of channel A and B; <b>Low = OFF, High = ON</b> . Controls LV1A, LV1B. High impedance input.
CWINA	CW gate input signal for A output. An input '1' means that current sinks from OUTA. An input '0' means that current sources from OUTA. This pin directly accesses the output A CW FET gates.
CWINB	CW gate input signal for B output. An input '1' means that current sinks from OUTB. An input '0' means that current sources from OUTB. This pin directly accesses the output B CW FET gates.
$\overline{\text{EN}}$	Logic Input for non-CW path; use the Enable-pin to select between input data being latched or transparent operation. Low = input data will be retimed by the internal (T&H) at the rate of the applied clock at PCLKIN. High = use this mode when operating the TX517 without a clock. When High (1) the input data will bypass the (T&H). This pin is a common control for Channel A and B. High impedance input.
$\overline{\text{PDM}}$	Power-down control input non-CW path; Low = power-down, High = normal operation. The $\overline{\text{PDM}}$ -pin controls the voltage translation circuits which draw some quiescent power. This pin is a common control for Channel A and B. High impedance input.
PCLKIN	Clock input for usage in latch (T&H) mode. When clock signal is high, the (T&H) circuit is in track mode. When clock signal is low, the (T&H) is in hold mode. This pin is a common clock input for both Channel A and B. High impedance input.
<b>OUTPUTS</b>	
OUTA	Output Channel A
OUTB	Output Channel B

## ABSOLUTE MAXIMUM RATINGS

Voltages referenced to Ground potential (GND = 0V); over operating free-air temperature (unless otherwise noted) <sup>(1)</sup>

		VALUE	UNIT
V <sub>DS</sub>	High-Voltage, Positive Supply HV1,2 referred to OUTA/B, see also Max. delta voltage	-0.3 to +80	V
	High-Voltage, Positive Supply HV0 referred to OUTA/B, see also Max. delta voltage	-0.3 to +6	V
	High-Voltage VCWA/B supply referred to GNDCWA/B	-0.3 to +16	V
V <sub>DS</sub>	High-Voltage, Negative Supply LV1,2 referred to OUTA/B, see also Max. delta voltage	-40 to +0.3	V
	High-Voltage, Negative Supply LV0 referred to OUTA/B, see also Max. delta voltage	-6 to +0.3	V
	Max. delta voltage: HV1-LV1 and HV2 – LV2	110	V
	Max. delta voltage: HV0 – LV0	12	V
VDD	Driver Supply, positive	-0.3 to +6	V
VEE	Driver Supply, negative	-6 to +0.3	V
VAA	Logic Supply Voltage	-0.3 to +6	V
	Logic Inputs (INPx, INNx, $\overline{EN}$ , $\overline{PDM}$ , PCLKIN, U)	-0.3 to +6	V
	CW inputs (CWINA, CWINB)	-0.3 to +11	V
	Peak Solder Temperature <sup>(2)</sup>	260	°C
TJ	Maximum junction temperature, any condition <sup>(3)</sup>	150	°C
TJ	Maximum junction temperature, continuous operation, long term reliability <sup>(4)</sup>	125	°C
Tstg	Storage temperature range	-65 to 150	°C
ESD ratings	HBM	500	V
	CDM	750	V
	MM	200	V

- (1) Stresses above those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute maximum rated conditions for extended periods may degrade device reliability.
- (2) Device complies with JSTD-020D.
- (3) The absolute maximum junction temperature under any condition is limited by the constraints of the silicon process.
- (4) The absolute maximum junction temperature for continuous operation is limited by the package constraints. Operation above this temperature may result in reduced reliability and/or lifetime of the device.

## THERMAL INFORMATION

THERMAL METRIC <sup>(1)</sup>		TX517	UNITS
		BGA (144) (ZCQ) PINS	
$\theta_{JA}$	Junction-to-ambient thermal resistance	28	°C/W
$\theta_{JCTop}$	Junction-to-case (top) thermal resistance	3.8	
$\theta_{JB}$	Junction-to-board thermal resistance	11.3	
$\psi_{JT}$	Junction-to-top characterization parameter	0.2	
Power Rating <sup>(2)(3)</sup> (TJ = 125°C)	TA = 25°C	3.57	W
	TA = 85°C	1.47	

- (1) 有关传统和新的热度的更多信息，请参阅 IC 封装热量量 应用报告 [SPRA953](#)。
- (2) This data was taken with the JEDEC High-K test PCB.
- (3) Power rating is determined with a junction temperature of 125°C. This is the point where distortion starts to substantially increase and long-term reliability starts to be reduced. Thermal management of the final PCB should strive to keep the junction temperature at or below 125°C for best performance and reliability.

**RECOMMENDED OPERATING CONDITIONS**

	<b>MIN</b>	<b>TYP</b>	<b>MAX</b>	<b>UNIT</b>
VAA	2.38	2.5	3.3	V
VDD	4.75	5.0	5.25	V
VEE	-5.25	-5.0	-4.75	V
HV0A, HV0B	0	1.9	5	V
LV0A, LV0B	-5	-1.9	0	V
HV2A, HV2B	0	32	70	V
LV2A, LV2B	-30	-11.9	0	V
HV1A, HV1B	>HV0 and >HV2	61	70	V
LV1A, LV1B	-30	-20.9	<LV0 and <LV2	V
VCWA, VCWB	0	11	15	V
Maximum DELTA between HV1 to LV1 and HV2 to LV2			100	V
INN <sub>x</sub> , INP <sub>x</sub> , $\overline{EN}$ , $\overline{PDM}$ , PCLKIN, U	0		VAA	V
INCWA, INCWB	0	5	10	V
INN <sub>xx</sub> , INP <sub>xx</sub> input sample rate	1		100	Msp/s
INN <sub>xx</sub> , INP <sub>xx</sub> input unit interval	10		1000	ns
PCLKIN input frequency	1		100	MHz
Ambient Temperature, T <sub>A</sub>	0		85	°C

## ELECTRICAL CHARACTERISTICS

All Specifications at:  $T_A = 0$  to  $85^\circ\text{C}$ ,  $V_{AA} = 2.5\text{V}$ ,  $V_{DD} = 5\text{V}$ ,  $V_{EE} = -5\text{V}$ ,  $HV_0 = 1.9\text{V}$ ,  $LV_0 = -1.9\text{V}$ ,  $HV_2 = 32\text{V}$ ,  $LV_2 = -11.9\text{V}$ ,  $HV_1 = +61.1\text{V}$ ,  $LV_1 = -20.9\text{V}$ ,  $V_{CW} = 11\text{V}$ ,  $R_L = 100\ \Omega$  to GND for OUTA,  $R_L = 100\ \Omega$  to GND for OUTB, unless otherwise noted. The parameter results are applicable to both OUTA and OUTB, and they are measured using Non-Latch Mode unless otherwise noted.

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS	TEST LEVEL <sup>(1)</sup>
<b>HV0/LV0 SIGNAL PATH – DC PERFORMANCE</b>							
<b>P-CHANNEL</b>							
	Effective resistance, $R_{DSon} + R_{diode}$	$HV_0 = 2\text{ V}$ , $OUTX = -750\text{ mV}$ to $-1.25\text{ V}$	6.5	9.5	13	$\Omega$	A
	Effective resistance variation	Max output power to Min output power, load = $100\ \Omega$ to $0\ \text{V}$			12%		C
	Output saturation current	$R_L = 5\ \Omega$ to $-30\ \text{V}$	-3.1	-1.3	-1	A	A
	Output voltage			1.0		V	C
<b>N-CHANNEL</b>							
	Effective resistance, $R_{DSon} + R_{diode}$	$LV_0 = -2\text{V}$ , $OUTX = 750\text{ mV}$ to $1.25\text{ V}$	2.5	5	8.5	$\Omega$	A
	Effective Resistance Variation	Max output power to Min output power, Load = $100\ \Omega$ to $0\ \text{V}$			5	%	C
	Output saturation current	$R_L = 5\ \Omega$ to $+30\ \text{V}$	1.4	1.8	3.1	A	A
	Output voltage			-1.2		V	C
<b>HV0/LV0 SIGNAL PATH – AC PERFORMANCE</b>							
	Single-tone output frequency		1		100	Msp/s	B
	2 <sup>nd</sup> Order harmonic distortion (when using transformer bridge)	$f = 5.0\text{ MHz}$ square wave, measured using transformer at secondary coil with $R_L = 100\ \Omega$		35		dBc	C
$t_r$	Output rise time	10% to 90% of $0\ \text{V}$ to $+V_{out}$ <a href="#">Figure 8</a>		4.5		ns	C
$t_f$	Output fall time	10% to 90% of $0\ \text{V}$ to $-V_{out}$ <a href="#">Figure 8</a>		1		ns	C
$t_{pr}$ , $t_{pf}$	Propagation Delay	Input 50% to Output 50% <a href="#">Figure 8</a>		30		ns	B
<b>HV2/LV2 SIGNAL PATH – DC PERFORMANCE</b>							
<b>P-CHANNEL</b>							
	Effective resistance, $R_{DSon} + R_{diode}$	$HV_2 = 30\ \text{V}$ to $HV_2 = 20\ \text{V}$	4.5	9	12.5	$\Omega$	A
	Effective resistance variation	Max output power to Min output power, load = $100\ \Omega$ to $0\ \text{V}$			12%		C
	Output saturation current	$HV_2 = 60\ \text{V}$ ; $R_L = 5\ \Omega$ to GND	-4.1	-2.3	-1.8	A	A
	Output voltage			28.5		V	C
<b>N-CHANNEL</b>							
	Effective resistance, $R_{DSon} + R_{diode}$	$LV_2 = -10\ \text{V}$ to $LV_2 = -12\ \text{V}$	1.5	4.5	7.5	$\Omega$	A
	Effective resistance variation	Max output power to Min output power, load = $100\ \Omega$ to $0\ \text{V}$			4%		C
	Output saturation current	$LV_2 = -60\ \text{V}$ ; $R_L = 5\ \Omega$ to GND	2.4	3.0	5.0	A	A
	Output Voltage			-10.5		V	C
<b>HV2/LV2 SIGNAL PATH – AC PERFORMANCE</b>							
	Single-tone Output Frequency		1		100	Msp/s	B
	2 <sup>nd</sup> Order harmonic distortion when using transformer bridge	$f = 5.0\text{ MHz}$ square wave, measured using transformer at secondary coil with $R_L = 100\ \Omega$		50		dBc	C
$t_r$	Output rise time	10% to 90% of $0\ \text{V}$ to $+V_{out}$ <a href="#">Figure 8</a>		7.5		ns	C
$t_f$	Output fall time	10% to 90% of $0\ \text{V}$ to $-V_{out}$ <a href="#">Figure 8</a>		3		ns	C
$t_{pr}$ , $t_{pf}$	Propagation delay	Input 50% to Output 50% <a href="#">Figure 8</a>		25		ns	B

- (1) Test levels: (A) 100% tested at  $25^\circ\text{C}$ . Over temperature limits by characterization and simulation. (B) Limits set by characterization and simulation. (C) Typical value only for information.

## ELECTRICAL CHARACTERISTICS

All Specifications at:  $T_A = 0$  to  $85^\circ\text{C}$ ,  $V_{AA} = 2.5\text{V}$ ,  $V_{DD} = 5\text{V}$ ,  $V_{EE} = -5\text{V}$ ,  $HV_0 = 1.9\text{V}$ ,  $LV_0 = -1.9\text{V}$ ,  $HV_2 = 32\text{V}$ ,  $LV_2 = -11.9\text{V}$ ,  $HV_1 = +61.1\text{V}$ ,  $LV_1 = -20.9\text{V}$ ,  $VCW = 11\text{V}$ ,  $R_L = 100\Omega$  to GND for OUTA,  $R_L = 100\Omega$  to GND for OUTB, unless otherwise noted. The parameter results are applicable to both OUTA and OUTB, and they are measured using Non-Latch Mode unless otherwise noted.

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	TEST LEVEL <sup>(1)</sup>
<b>HV1/LV1 SIGNAL PATH – DC PERFORMANCE</b>						
<b>P-CHANNEL</b>						
Effective resistance, $R_{DSon} + R_{diode}$	$HV_1 = 60\text{V}$ to $HV_1 = 50\text{V}$	2.5	7	12.5	$\Omega$	A
Effective resistance variation	Max output power to Min output power load = $100\Omega$ to GND			11%		C
Output saturation current	$HV_1 = 60\text{V}$ ; $R_L = 5\Omega$ to GND	-4.1	-2.5	-2	A	A
Output voltage			58		V	C
<b>N-CHANNEL</b>						
Effective resistance, $R_{DSon} + R_{diode}$	$LV_1 = -20\text{V}$ to $-10\text{V}$	1	2	4.5	$\Omega$	A
Effective resistance variation	Max output power to Min output power load = $100\Omega$ to $0\text{V}$			3%		C
Output saturation current	$LV_1 = -60\text{V}$ ; $R_L = 5\Omega$ to GND	2.9	3.4	4.1	A	A
Output voltage			-20		V	C
<b>HV1/LV1 SIGNAL PATH – AC PERFORMANCE</b>						
Single-tone output frequency		1		100	Msp/s	B
2 <sup>nd</sup> Order harmonic distortion (when using transformer bridge)	$f = 5.0\text{MHz}$ square wave, measured using transformer at secondary coil with $R_L = 100\Omega$		60		dBc	C
$t_r$ Output rise time	10% to 90% of $0\text{V}$ to $+V_{out}$ <a href="#">Figure 8</a>		6.5		ns	C
$t_f$ Output fall time	10% to 90% of $0\text{V}$ to $-V_{out}$ <a href="#">Figure 8</a>		3		ns	C
$t_{pr}$ , $t_{pf}$ Propagation Delay	Input 50% to Output 50% <a href="#">Figure 8</a>		25		ns	B

- (1) Test levels: (A) 100% tested at  $25^\circ\text{C}$ . Over temperature limits by characterization and simulation. (B) Limits set by characterization and simulation. (C) Typical value only for information.

## ELECTRICAL CHARACTERISTICS

All Specifications at:  $T_A = 0$  to  $85^\circ\text{C}$ ,  $V_{AA} = 2.5\text{V}$ ,  $V_{DD} = 5\text{V}$ ,  $V_{EE} = -5\text{V}$ ,  $HV_0 = 1.9\text{V}$ ,  $LV_0 = -1.9\text{V}$ ,  $HV_2 = 32\text{V}$ ,  $LV_2 = -11.9\text{V}$ ,  $HV_1 = +61.1\text{V}$ ,  $LV_1 = -20.9\text{V}$ ,  $VCW = 11\text{V}$ ,  $R_L = 100\Omega$  to GND for OUTA,  $R_L = 100\Omega$  to GND for OUTB, unless otherwise noted. The parameter results are applicable to both OUTA and OUTB, and they are measured using Non-Latch Mode unless otherwise noted.

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	TEST LEVEL <sup>(1)</sup>
<b>CW SIGNAL PATH – DC PERFORMANCE</b>						
<b>P-CHANNEL</b>						
Effective resistance, $R_{DSon} + R_{diode}$	$VCW = 4.5\text{V}$ to $5.5\text{V}$	9	21	31	$\Omega$	A
Effective resistance variation	Max output power to Min output power, load = $100\Omega$ to $0\text{V}$			30%		C
Output saturation current	$R_L = 5\Omega$ to $-20\text{V}$	-0.16	-0.12	-0.06	A	A
Output voltage			8		V	C
<b>N-CHANNEL</b>						
Effective resistance, $R_{DSon} + R_{diode}$	$OUTX = 1\text{V}$ to $2\text{V}$	9	14	18	$\Omega$	A
Effective resistance variation	Max output power to Min output power, load = $100\Omega$ to $0\text{V}$			10%		C
Output saturation current	$R_L = 5\Omega$ to $20\text{V}$	0.29	0.35	0.44	A	A
Output voltage			30		mV	C

- (1) Test levels: (A) 100% tested at  $25^\circ\text{C}$ . Over temperature limits by characterization and simulation. (B) Limits set by characterization and simulation. (C) Typical value only for information.

## ELECTRICAL CHARACTERISTICS (continued)

All Specifications at:  $T_A = 0$  to  $85^\circ\text{C}$ ,  $V_{AA} = 2.5\text{V}$ ,  $V_{DD} = 5\text{V}$ ,  $V_{EE} = -5\text{V}$ ,  $HV0 = 1.9\text{V}$ ,  $LV0 = -1.9\text{V}$ ,  $HV2 = 32\text{V}$ ,  $LV2 = -11.9\text{V}$ ,  $HV1 = +61.1\text{V}$ ,  $LV1 = -20.9\text{V}$ ,  $V_{CW} = 11\text{V}$ ,  $R_L = 100\ \Omega$  to GND for OUTA,  $R_L = 100\ \Omega$  to GND for OUTB, unless otherwise noted. The parameter results are applicable to both OUTA and OUTB, and they are measured using Non-Latch Mode unless otherwise noted.

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS	TEST LEVEL <sup>(1)</sup>
<b>CW SIGNAL PATH – AC PERFORMANCE<sup>(2)</sup></b>							
Single-tone output frequency			0.5		10	MHz	B
2 <sup>nd</sup> Order harmonic distortion	f = 1 MHz, measured using transformer at secondary coil with $R_L = 100\ \Omega$			47		dBc	C
	f = 5 MHz, measured using transformer at secondary coil with $R_L = 100\ \Omega$			33		dBc	C
Slew Rate + (Positive Edge)		20% to 80% of $V_{outpp}$ , measured using transformer at secondary coil with $R_L = 100\ \Omega$		0.6		V/ns	C
Slew Rate – (Negative Edge)				0.45		V/ns	C
$t_r$	Output rise time	10% to 90% of 0 V to +Vout Figure 8		30		ns	C
$t_f$	Output fall time	10% to 90% of 0 V to –Vout Figure 8		10		ns	C
$t_{pr}$ , $t_{pf}$	Propagation Delay	Input 50% to Output 50% Figure 8		25		ns	B
AC-coupled gate drive time constant for P-CHANNEL			10	20	30	$\mu\text{s}$	C
<b>CW INPUT CHARACTERISTIC</b>							
High input voltage			1.05			V	B
Low input voltage					0.35	V	B
Low input current		CWINX=0V		0	1	$\mu\text{A}$	B
High input current		CWINX=5.0V		25	40	$\mu\text{A}$	B
Input Gate Charge		CWINX = 0 V to 5.0 V or 5.0 V to 0 V		550		pC	C
<b>LOGIC CHARACTERISTICS – INNxx, INPxx, EN, PDM, PCLKIN pins</b>							
Input capacitance	INNxx, INPxx, PCLKIN @ 10 MHz			6		pF	C
	EN @ 10 MHz			9			
	PDM @ 10 MHz			4			
Logic high input voltage		VAA=2.375V to 3.6V	0.55*VAA		VAA	V	B
Logic low input voltage		VAA=2.375V to 3.6V	0		0.8	V	B
Logic low input current				0.2	10	$\mu\text{A}$	B
Logic high input current				0.2	10	$\mu\text{A}$	B
Minimum clock period, $t_{per}$		Figure 9, PCLKIN		10		ns	B
Minimum clock high time, $t_{min}$		Figure 9, PCLKIN		2.0		ns	B
$t_s$	Setup time	Figure 9, PCLKIN, INNxx, INPxx		0		ns	B
$t_h$	Hold time	Figure 9, PCLKIN, INNxx, INPxx		1.5		ns	B
<b>OUTPUT CHARACTERISTIC</b>							
Output resistance		Power Down Mode (Hi-Z Output) $V_{TEST} = 20\ \text{V}$		1		$\text{G}\Omega$	C
Output capacitance		Power Down Mode (Hi-Z Output) @1 to 100 MHz		165		pF	C
Leakage current		Power Down Mode (Hi-Z Output) $V_{TEST} = 0\ \text{V}$		0.001	10	$\mu\text{A}$	A
<b>INTERNAL GATE CHARGE CHARACTERISTICS</b>							
Input gate charge <sup>(3)</sup>	HV0/LV0 internal FET gates driven from VEE to VDD or VDD to VEE			3.5		nC	C
	HV1/LV1 internal FET gates driven from VEE to VDD or VDD to VEE			4.6		nC	C
	HV2/LV2 internal FET gates driven from VEE to VDD or VDD to VEE			7		nC	C

- (1) Test levels: (A) 100% tested at  $25^\circ\text{C}$ . Over temperature limits by characterization and simulation. (B) Limits set by characterization and simulation. (C) Typical value only for information.
- (2) TX517 CW outputs are complimentary. Thus a transformer is needed to enable CW output.
- (3) Input gate charge is the amount of charge to change the internal FET gates of a given output from either a low to a high state or from a high to a low state. Each gate charge value applies to both the P and N type FET for the given output. These values can be used to estimate the amount of dynamic current that needs to be provided to the VDD and VEE power supplies in order to switch the internal FET's at a given sampling rate.

## ELECTRICAL CHARACTERISTICS

All Specifications at:  $T_A = 0$  to  $85^\circ\text{C}$ ,  $V_{AA} = 2.5\text{V}$ ,  $V_{DD} = 5\text{V}$ ,  $V_{EE} = -5\text{V}$ ,  $HV0 = 1.9\text{V}$ ,  $LV0 = -1.9\text{V}$ ,  $HV2 = 32\text{V}$ ,  $LV2 = -11.9\text{V}$ ,  $HV1 = +61.1\text{V}$ ,  $LV1 = -20.9\text{V}$ ,  $V_{CW} = 11\text{V}$ ,  $R_L = 100\Omega$  to GND for OUTA,  $R_L = 100\Omega$  to GND for OUTB, unless otherwise noted. The parameter results are applicable to both OUTA and OUTB, and they are measured using Non-Latch Mode unless otherwise noted.

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	TEST LEVEL <sup>(1)</sup>		
<b>POWER SUPPLY</b>								
Total Quiescent Current (PW Mode) Power supply VDD	INPxx = 1, INNxx = 0, PCLKIN= 0 or 1		13	15	mA	A		
Total Quiescent Current (PW Mode) Power supply VEE	INPxx = 1, INNxx = 0, PCLKIN= 0 or 1	-10	-8		mA	A		
Total Quiescent Current (PW Mode) Power supply VAA	INPxx = 1, INNxx = 0, PCLKIN= 0 or 1	-3	-2		mA	A		
Dynamic Current Consumption (PW Mode) Power supply VDD	Input pattern = 10 cycle square wave, 5% duty cycle at 10 Msps (5 MHz) on noted signal path. Load = transformer and 100 ohm differential load, see Figure 10.	HV0/LV0		17	23	mA	B	
			HV1/LV1		18			23
			HV2/LV2		20.5			23
Dynamic Current Consumption (PW Mode) Power supply VEE	Input pattern = 10 cycle square wave, 5% duty cycle at 10 Msps (5 MHz) on noted signal path. Load = transformer and 100 ohm differential load, see Figure 10.	HV0/LV0		-15	-10	mA	B	
			HV1/LV1		-15			-10.5
			HV2/LV2		-15			-12.5
Dynamic Current Consumption (PW Mode) Power supply VAA	Input pattern = 10 cycle square wave, 5% duty cycle at 10 Msps (5 MHz) on noted signal path. Load = transformer and 100 ohm differential load, see Figure 10.	HV0/LV0		-4	-2.3	mA	B	
			HV1/LV1		-4			-2.5
			HV2/LV2		-4			-2.5
Dynamic Current Consumption (PW Mode) Power supply HV0	Input pattern = 10 cycle square wave, 5% duty cycle at 10 Msps (5 MHz) on noted signal path. Load = transformer and 100 ohm differential load, see Figure 10.		2	4	mA	B		
Dynamic Current Consumption (PW Mode) Power supply LV0	Input pattern = 10 cycle square wave, 5% duty cycle at 10 Msps (5 MHz) on noted signal path. Load = transformer and 100 ohm differential load, see Figure 10.	-3.5	-2		mA	B		
Dynamic Current Consumption (PW Mode) Power supply HV1	Input pattern = 10 cycle square wave, 5% duty cycle at 10 Msps (5 MHz) on noted signal path. Load = transformer and 100 ohm differential load, see Figure 10.		41	60	mA	B		
Dynamic Current Consumption (PW Mode) Power supply LV1	Input pattern = 10 cycle square wave, 5% duty cycle at 10 Msps (5 MHz) on noted signal path. Load = transformer and 100 ohm differential load, see Figure 10.	-55	-41		mA	B		
Dynamic Current Consumption (PW Mode) Power supply HV2	Input pattern = 10 cycle square wave, 5% duty cycle at 10 Msps (5 MHz) on noted signal path. Load = transformer and 100 ohm differential load, see Figure 10.		22	60	mA	B		
Dynamic Current Consumption (PW Mode) Power supply LV2	Input pattern = 10 cycle square wave, 5% duty cycle at 10 Msps (5 MHz) on noted signal path. Load = transformer and 100 ohm differential load, see Figure 10.	-35	-22		mA	B		
Total Power Dissipation for device only (PW Mode)	Input pattern = 10 cycle square wave, 5% duty cycle at 10 Msps on noted signal path. Load = transformer and 100 ohm differential load, see Figure 10.	HV0/LV0		0.15	0.25	W	B	
		HV1/LV1		1.1	1.7			
		HV2/LV2		0.6	0.8			
Dynamic Current Consumption (CW Mode) Power supply VCWA + VCWB	Input pattern = 10 cycle square wave, 100% duty cycle at 10 Msps on CW signal path. Load = transformer and 100 ohm differential load, see Figure 10. EN <sub>1</sub> = 0 or 1, PCLKIN = 0 or 1		62	100	mA	B		
Total Power Dissipation for device only (CW Mode)	Input pattern = 10 cycle square wave, 100% duty cycle at 10 Msps (5 MHz) on noted signal path. Load = transformer and 100 ohm differential load, see Figure 10. EN <sub>1</sub> = 0 or 1, PCLKIN = 0 or 1		310	400	mW	B		
Supply (HVx, LVx) Slew Rate Limit				10	V/ms	B		
<b>POWER-DOWN CHARACTERISTIC</b>								
Power-Down Dissipation	Power Down Mode (Hi-Z Output) PDM <sub>1</sub> = 0, INPxx = 1, INNxx = 0 PCLKIN = 0 or 1		3	15	mW	A		

(1) Test levels: (A) 100% tested at  $25^\circ\text{C}$ . Over temperature limits by characterization and simulation. (B) Limits set by characterization and simulation. (C) Typical value only for information.

## ELECTRICAL CHARACTERISTICS (any level to any level transitions – 17 level output, 289 unique transitions<sup>(1)</sup>)

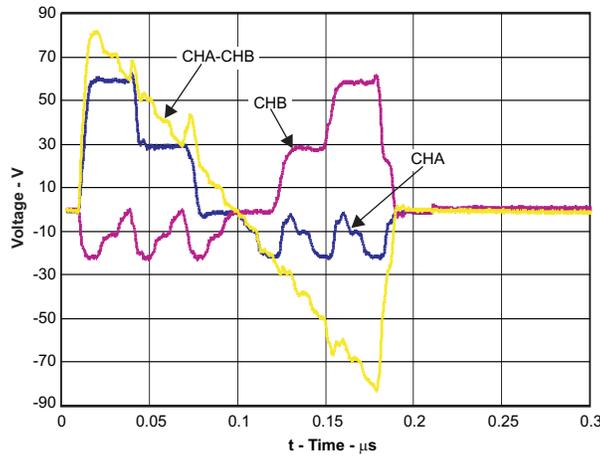
All Specifications at:  $T_A = 0^\circ\text{C}$  to  $85^\circ\text{C}$ ,  $V_{AA} = 2.5\text{V}$ ,  $V_{DD} = 5\text{V}$ ,  $V_{EE} = -5\text{V}$ ,  $HV0 = 1.9\text{V}$ ,  $LV0 = -1.9\text{V}$ ,  $HV2 = 32\text{V}$ ,  $LV2 = -11.9\text{V}$ ,  $HV1 = +61.1\text{V}$ ,  $LV1 = -20.9\text{V}$ ,  $V_{CW} = 11\text{V}$ ,  $R_L = 100\ \Omega$  to GND for OUTA,  $R_L = 100\ \Omega$  to GND for OUTB, unless otherwise noted.

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	TEST LEVEL <sup>(2)</sup>
<b>POWER UP/DOWN TIMING</b>						
Power down time			100		ns	C
Power up time			100		ns	C
<b>HVX/LVX SIGNAL PATH – AC PERFORMANCE</b>						
Mean normalized output rise time	10% to 90% of 0 to 1, 20MHz		5		ns	C
Mean delay (relative to clock edge of 1 <sup>st</sup> sample)	0-20 MHz		23		ns	C
Delay standard deviation	0-20 MHz		1.2		ns	C
Phase standard deviation	5 MHz		0.01		cycles	C
	20 MHz		0.03		cycles	C
Gain standard deviation	5 MHz		4		%	C
	20 MHz		8		%	C

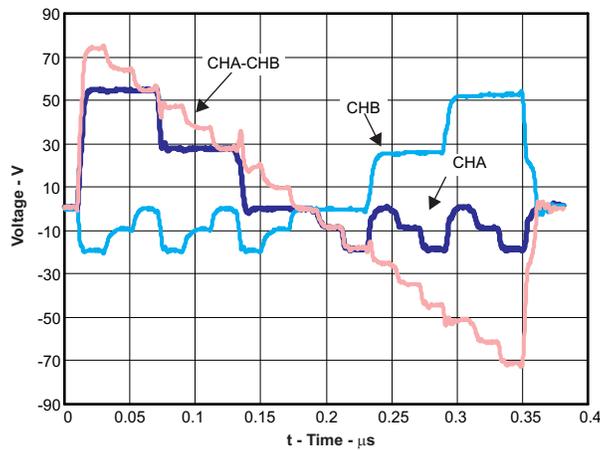
- (1) These parameters are measured on the differential output starting from 1 of 17 possible states to every other possible state. Therefore,  $17 \times 17 = 289$  unique transitions.
- (2) Test levels: (A) 100% tested at  $25^\circ\text{C}$ . Over temperature limits by characterization and simulation. (B) Limits set by characterization and simulation. (C) Typical value only for information.

**TYPICAL CHARACTERISTICS**

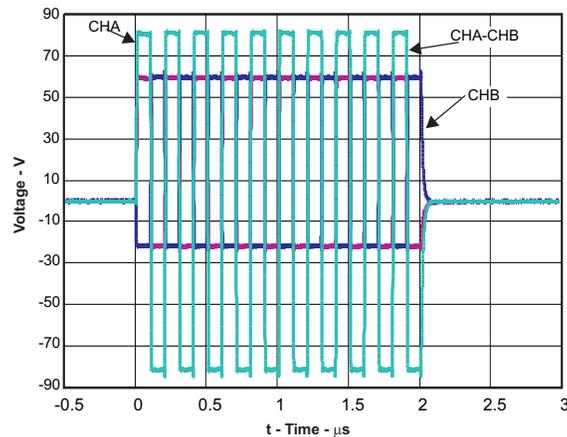
All Specifications at:  $T_A = 25^\circ\text{C}$ ,  $V_{AA} = +2.5\text{V}$ ,  $V_{DD} = +5\text{V}$ ,  $V_{EE} = -5\text{V}$ ,  $HV0 = 1.9\text{V}$ ,  $LV0 = -1.9\text{V}$ ,  $HV2 = 32\text{V}$ ,  $LV2 = -11.9\text{V}$ ,  $HV1 = +61.1\text{V}$ ,  $LV1 = -20.9\text{V}$ ,  $V_{CW} = 11\text{V}$ ,  $R_L = 100\Omega$  to GND for OUTA,  $R_L = 100\Omega$  to GND for OUTB, unless otherwise noted.



**Figure 1. 17-level Outputs with 10ns Pulse Width (100MSPS)**



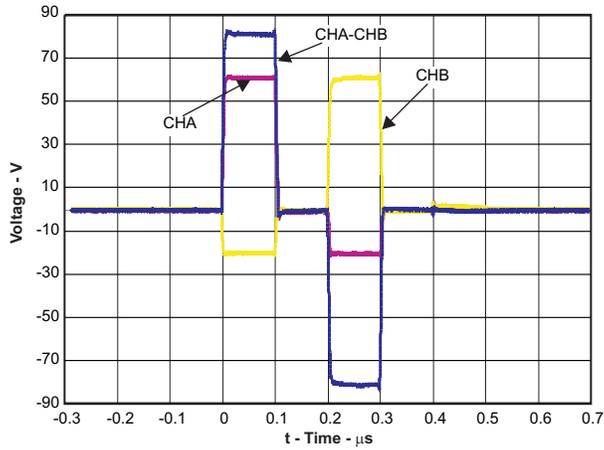
**Figure 2. 17-level Outputs with 20ns Pulse Width (50MSPS)**



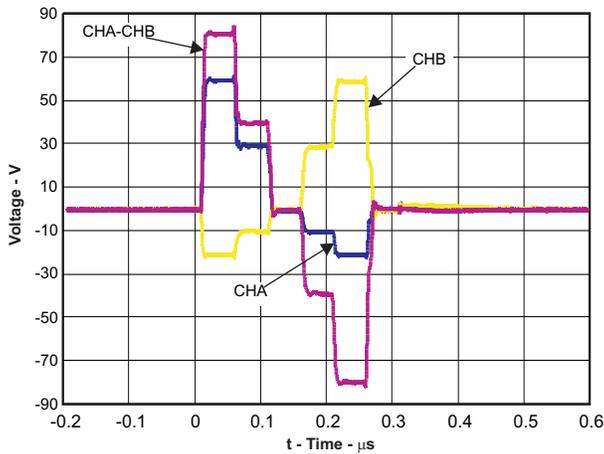
**Figure 3. 5MHz 3-level 10 Cycles Outputs**

**TYPICAL CHARACTERISTICS (continued)**

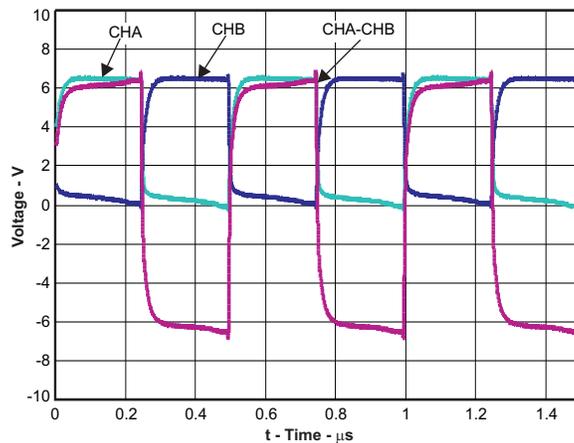
All Specifications at:  $T_A = 25^\circ\text{C}$ ,  $V_{AA} = +2.5\text{V}$ ,  $V_{DD} = +5\text{V}$ ,  $V_{EE} = -5\text{V}$ ,  $HV0 = 1.9\text{V}$ ,  $LV0 = -1.9\text{V}$ ,  $HV2 = 32\text{V}$ ,  $LV2 = -11.9\text{V}$ ,  $HV1 = +61.1\text{V}$ ,  $LV1 = -20.9\text{V}$ ,  $V_{CW} = 11\text{V}$ ,  $R_L = 100\Omega$  to GND for OUTA,  $R_L = 100\Omega$  to GND for OUTB, unless otherwise noted.



**Figure 4. 3-level Outputs with 100ns Pulse Width (10MSPS)**



**Figure 5. 5MHz 5-level Outputs**



**Figure 6. 2MHz CW Outputs**

## APPLICATION INFORMATION

**Table 1. Truth Table**

Description	$\overline{EN}$	$\overline{PDM}$	PCLKIN	CWINA	CWINB	INPxx <sup>(1)</sup>	INNxx <sup>(1)</sup>
Power Down (Hi-Z Output)	1	0	x <sup>(2)</sup>	0	0	1	0
CW Mode	x	0	x	0/1	1/0	1	0
Non-Latch Mode	1	1	x	0	0	0/1	0/1
Latch Mode	0	1	0/1	0	0	0/1	0/1

- (1) The logic device driving the inputs of the TX517 should include means to prevent a 'shoot-thru' fault condition. Any input combination that would result in an INP-input to be Low (0) and an INN-input to be High (1) at the same time on the same output (OUTA or OUTB) could result in permanent damage to the TX517. See also disallowed logic state table. [Table 3](#) is provided for an example of how to properly drive the TX517 data inputs INPxx and INNxx.
- (2) X = don't care state. However, in order to prevent excessive power consumption it is recommended that all unused inputs be tied off to a logic high or logic low. The logic inputs to the device have no internal tie-off's.

**Table 2. Disallowed Logic States**

Description	$\overline{EN}$	$\overline{PDM}$	PCLKIN	CWINA	CWINB	INPxA	INNxA	INPxB	INNxB
Disallowed mode 1 <sup>(1)</sup>	x	x	x	x	x	0	1	x	x
Disallowed mode 2 <sup>(1)</sup>	x	x	x	x	x	x	x	0	1
Disallowed mode 3 <sup>(2)</sup>	x	0	x	x	x	x	1	x	x
Disallowed mode 4 <sup>(2)</sup>	x	0	x	x	x	x	x	x	1
Disallowed mode 5 <sup>(2)</sup>	x	0	x	x	x	0	x	x	x
Disallowed mode 6 <sup>(2)</sup>	x	0	x	x	x	x	x	0	x
Disallowed mode 7 <sup>(3)</sup>	0	x	0	x	x	x	x	x	x

- (1) This logic state causes a 'shoot-thru' fault condition that could result in permanent damage to the TX517.
- (2) This logic state causes a high power consumption condition in the internal logic circuitry of the TX517 and could result in a long term reliability failure of the TX517.
- (3) This disallowed logic state is only valid for DC conditions. i.e. it is not allowed to keep PCLKIN at a low logic state when EN is at a low logic state. This causes a high power consumption condition in the internal logic circuitry of the TX517. However, it is acceptable to drive EN low and drive PCLKIN with a clock waveform under the recommended operating conditions for PCLKIN.

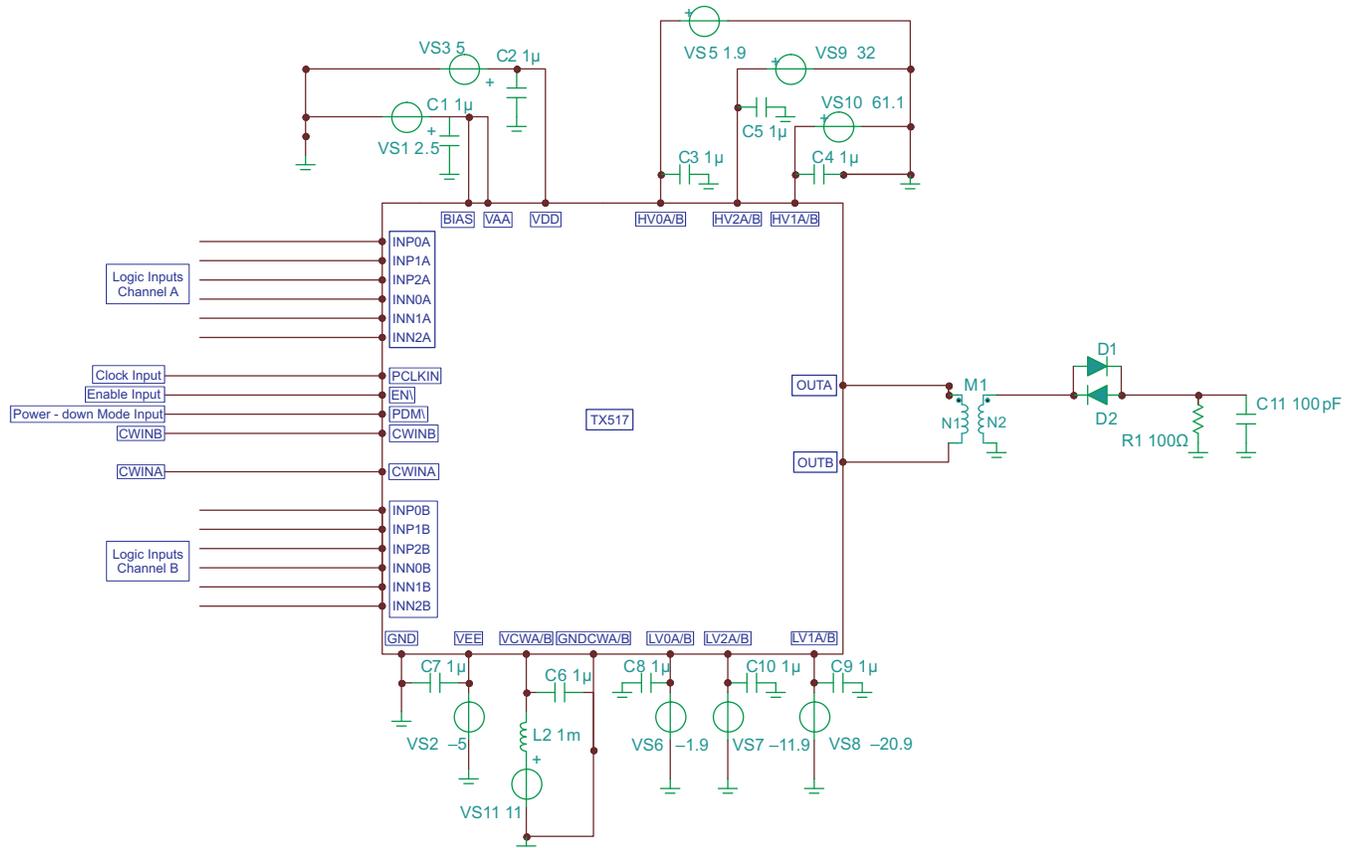
**Table 3. Example Input Data Set of a 17-Level Output<sup>(1)</sup>**

Output Level	INP0A	INP2A	INP1A	INP1B	INP2B	INP0B	INN0A	INN2A	INN1A	INN1B	INN2B	INN0B
8	0	0	1	0	0	0	0	0	0	1	0	0
7	0	0	1	0	0	0	0	0	0	0	1	0
6	0	0	1	0	0	1	0	0	0	0	0	1
5	0	1	0	0	0	0	0	0	0	1	0	0
4	0	1	0	0	0	0	0	0	0	0	1	0
3	0	1	0	0	0	1	0	0	0	0	0	1
2	1	0	0	0	0	0	1	0	0	1	0	0
1	1	0	0	0	0	0	1	0	0	0	1	0
0	1	0	0	0	0	1	1	0	0	0	0	1
-1	0	0	0	0	0	1	0	1	0	0	0	1
-2	0	0	0	0	0	1	0	0	1	0	0	1
-3	1	0	0	0	1	0	1	0	0	0	0	0
-4	0	0	0	0	1	0	0	1	0	0	0	0
-5	0	0	0	0	1	0	0	0	1	0	0	0
-6	1	0	0	1	0	0	1	0	0	0	0	0
-7	0	0	0	1	0	0	0	1	0	0	0	0
-8	0	0	0	1	0	0	0	0	1	0	0	0
off state	0	0	0	0	0	0	0	0	0	0	0	0

- (1) The levels listed in this table are active high; the P signals need to be inverted before driving the chip. This note is only applicable to THIS particular table ("the example input data set of a 17-level output).

**Table 4. Power Supplies Sequence**

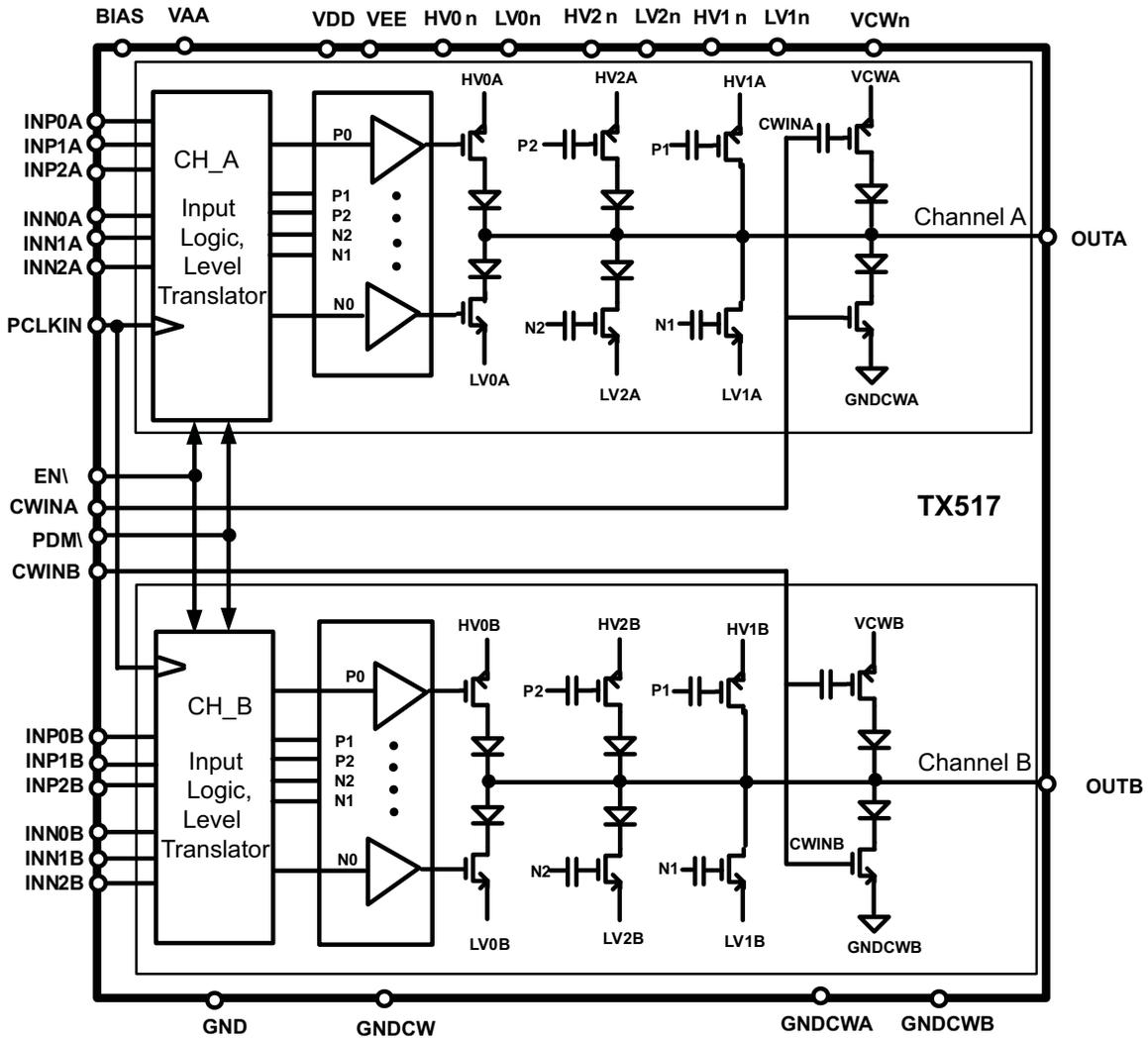
	1	2	3	4
Power-up	Driver Supplies(V <sub>EE</sub> , V <sub>AA</sub> , V <sub>DD</sub> )	LV1	HV1	LV2, LV0, HV0, HV2, VCW
Power-down	VCW, HV2, HV0, LV0, LV2	HV1	LV1	Driver Supplies (V <sub>DD</sub> , V <sub>AA</sub> , V <sub>EE</sub> )



- A. Diodes D1, D2 placeholders only; choose appropriate model (e.g. MMBD3004S)
- B. Load resistor R1, and capacitor C11 usage and values may vary depending on final configuration
- C. Bypass capacitors and values on all supplies are placeholders only. Capacitors between various supply rails may also be necessary.
- D. Inductors (ferrite beads) L1, L2 are optional components
- E. Voltages levels on the voltage supplies correspond to the ones used at simulation

**Figure 7. Typical Device Configuration**

BLOCK DIAGRAM



TIMING RELATED INFORMATION

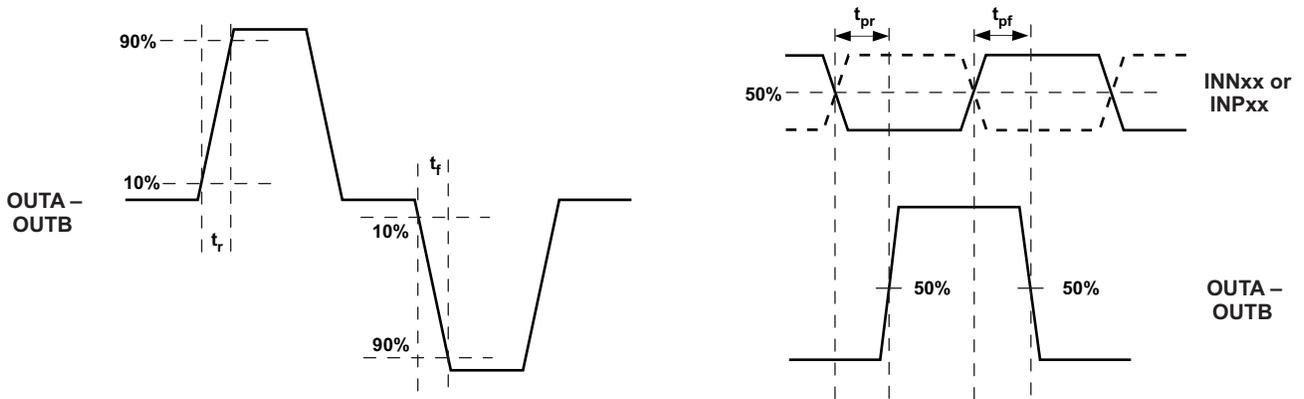


Figure 8. Output Timing Information

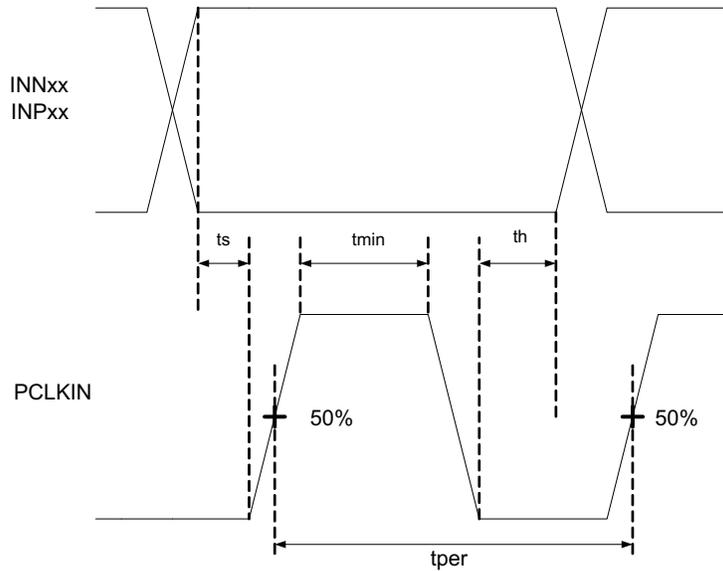


Figure 9. Timing Waveform for Latch Mode



**Note A:** This signal is supplied by a function generator with the following characteristics: 0 to 2.5V square wave,  $t_r/t_f < 3ns$ , frequency as noted in the electrical characteristics.

Figure 10. Loading for Power Consumption Tests

## REVISION HISTORY

<b>Changes from Original (September 2011) to Revision A</b>	<b>Page</b>
• Fixed duty cycle typo, changed duty cycle from 5% to 100% for "Dynamic Current Consumption (CW Mode) Power supply VCWA + VCWB" in the ELECTRICAL CHARACTERISTICS table. ....	<a href="#">9</a>
• Fixed duty cycle typo, changed duty cycle from 5% to 100% for "Total Power Dissipation for device only (CW Mode)" in the ELECTRICAL CHARACTERISTICS table. ....	<a href="#">9</a>

**PACKAGING INFORMATION**

Orderable part number	Status (1)	Material type (2)	Package   Pins	Package qty   Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
<a href="#">TX517IZCQ</a>	Active	Production	NFBGA (ZCQ)   144	160   JEDEC TRAY (5+1)	Yes	Call TI	Level-3-260C-168 HR	0 to 85	TX517I
TX517IZCQ.A	Active	Production	NFBGA (ZCQ)   144	160   JEDEC TRAY (5+1)	Yes	Call TI	Level-3-260C-168 HR	0 to 85	TX517I

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

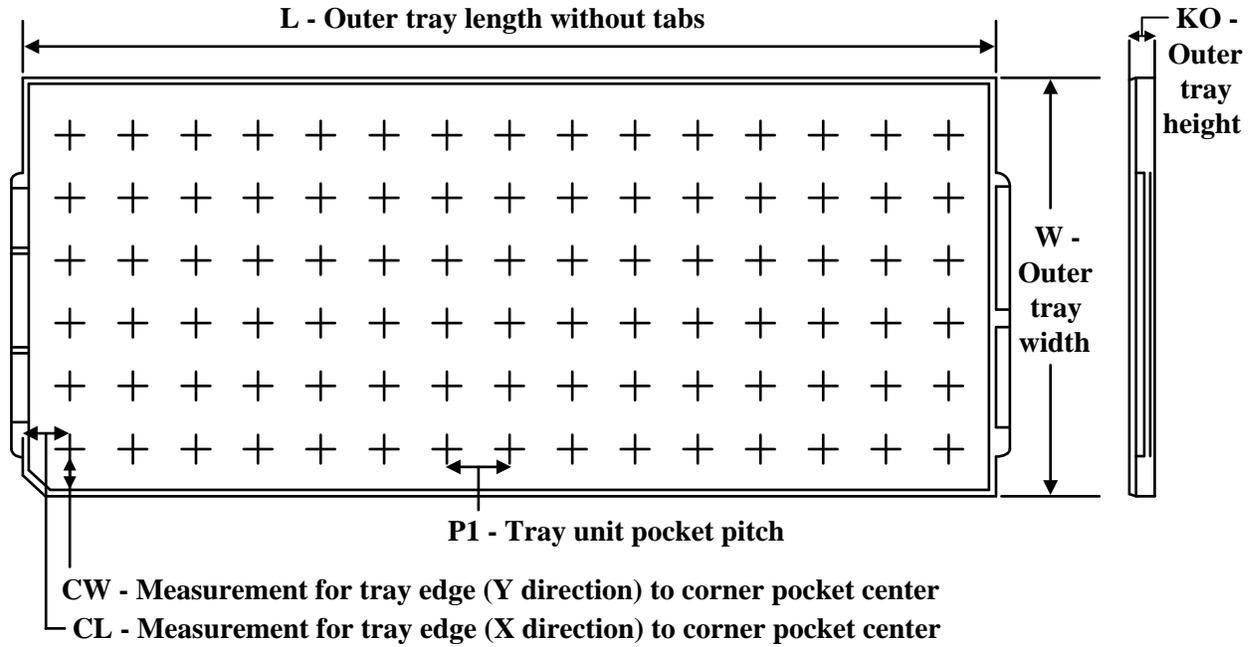
(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

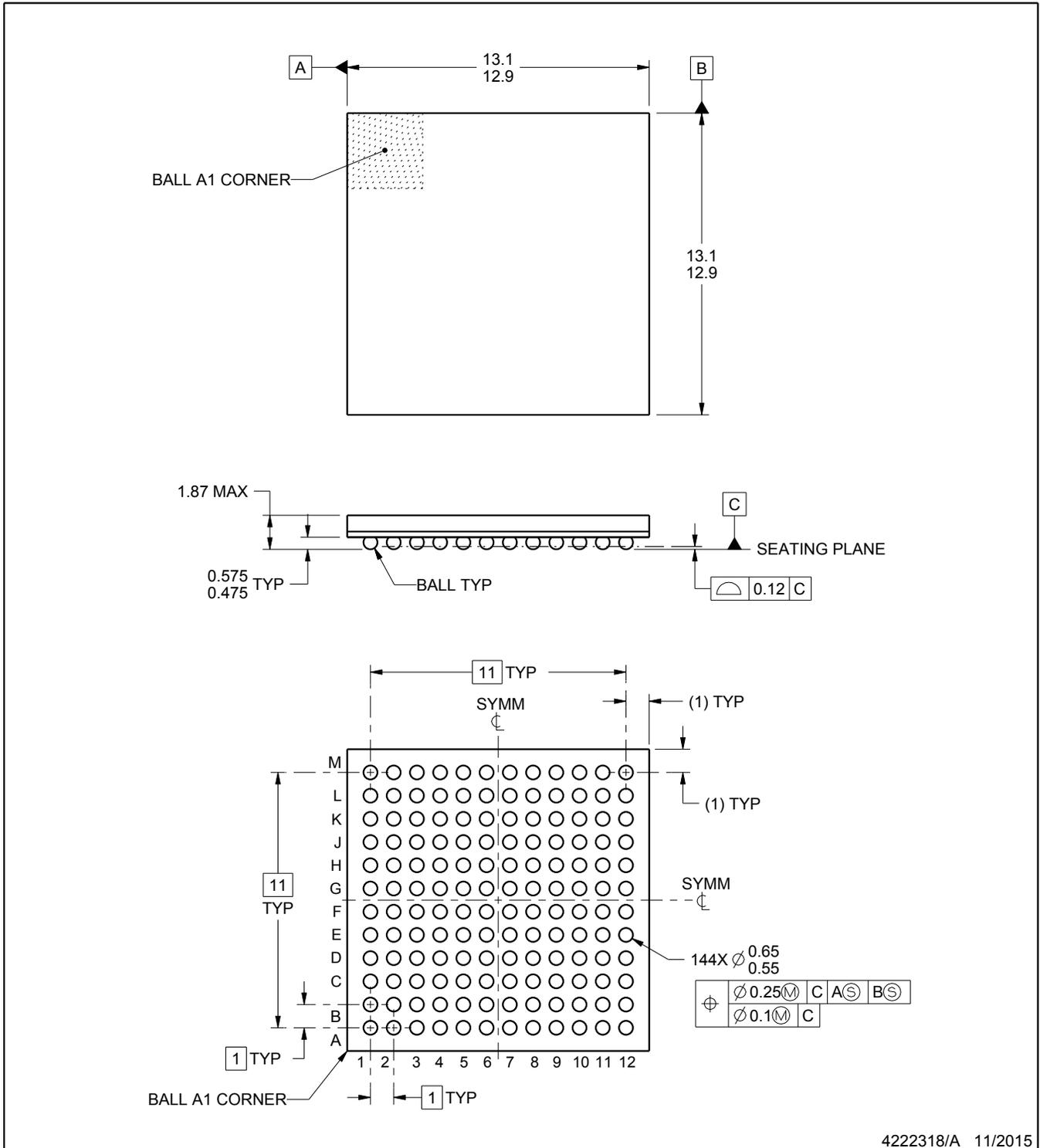
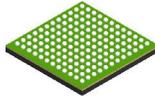
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

**TRAY**


Chamfer on Tray corner indicates Pin 1 orientation of packed units.

\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	Unit array matrix	Max temperature (°C)	L (mm)	W (mm)	K0 (µm)	P1 (mm)	CL (mm)	CW (mm)
TX517IZCQ	ZCQ	NFBGA	144	160	8 x 20	150	315	135.9	7620	15	15	15.45
TX517IZCQ.A	ZCQ	NFBGA	144	160	8 x 20	150	315	135.9	7620	15	15	15.45



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NOTES:

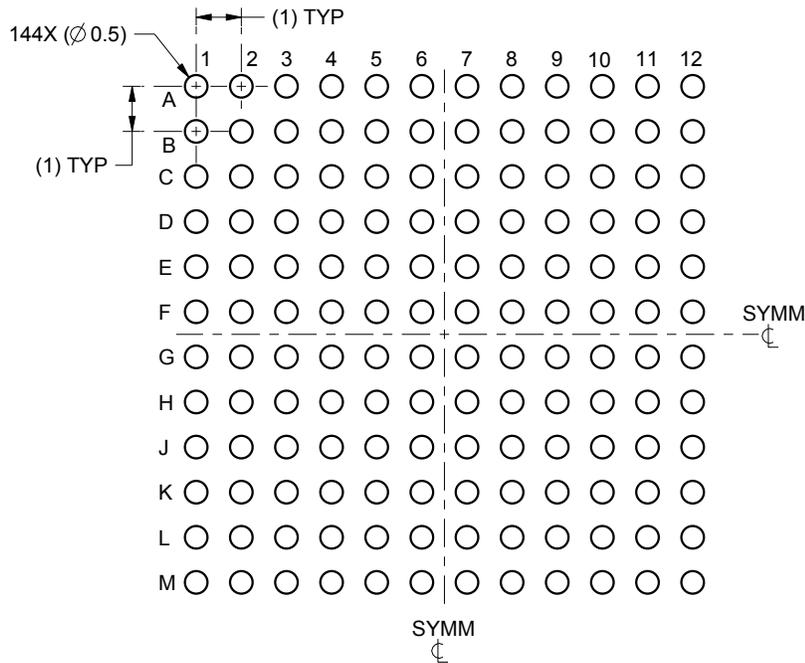
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

# EXAMPLE BOARD LAYOUT

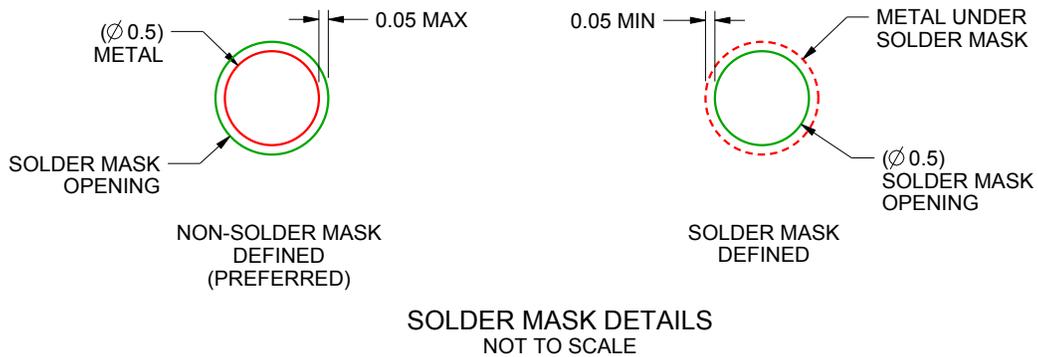
ZCQ0144A

NFBGA - 1.87 mm max height

PLASTIC BALL GRID ARRAY



LAND PATTERN EXAMPLE  
SCALE:6X



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NOTES: (continued)

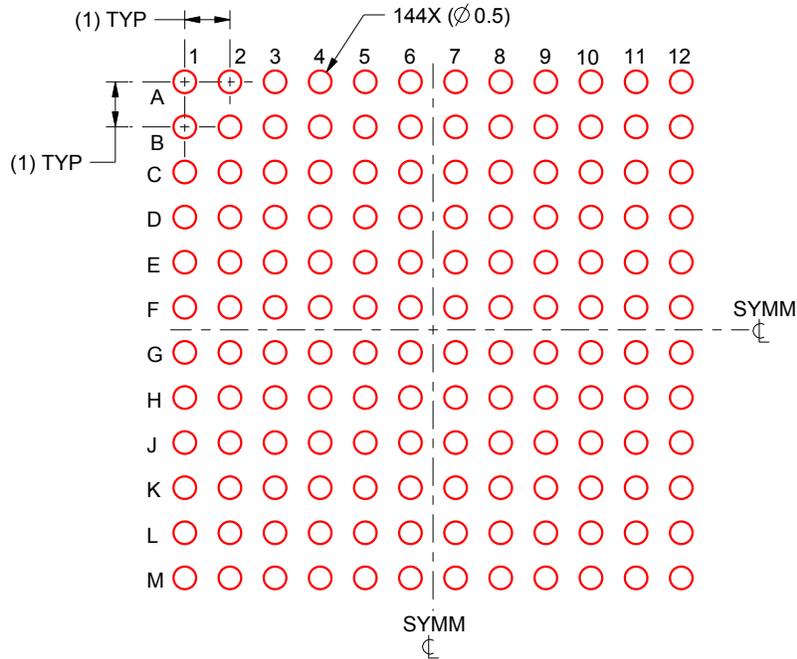
- Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For information, see Texas Instruments literature number SPRAA99 ([www.ti.com/lit/spraa99](http://www.ti.com/lit/spraa99)).

# EXAMPLE STENCIL DESIGN

ZCQ0144A

NFBGA - 1.87 mm max height

PLASTIC BALL GRID ARRAY



SOLDER PASTE EXAMPLE  
BASED ON 0.15 mm THICK STENCIL  
SCALE:6X

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NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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